

Features

- Uses CRM(CQ) advanced SkyMOS2 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- AEC-Q101 Qualified

Applications

- DCDC Converter
- Switching applications
- UPS (Uninterruptible Power Supplies)

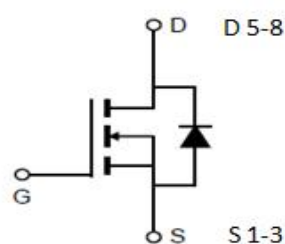
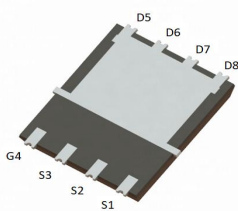
Product Summary

V_{DS}	60V
$R_{DS(on).typ}$	9.6mΩ
I_D	30A

100% DVDS Tested
100% Avalanche Tested



CRSMW120N06L2Q



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSMW120N06L2Q	120N06L2Q	PDFN5x6-WF	Tape&reel	N/A	N/A	4000pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	60	V
Continuous drain current	I_D	50	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		34	
$T_C = 100^\circ\text{C}$ (Silicon limit)			
Pulsed drain current ($T_C = 25^\circ\text{C}$, t_p limited by T_{jmax})	$I_{D\ pulse}$	120	A
Avalanche energy, single pulse ($I_{AS} = 19\text{A}$, $R_g=50\Omega$) ^[1]	E_{AS}	87	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation ($T_C = 25^\circ\text{C}$)	P_{tot}	42	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	°C
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	°C

※. Notes:

EAS is tested at starting $T_j = 25^\circ\text{C}$, $L = 0.3\text{mH}$, $I_{AS} = 19\text{A}$, $V_{GS} = 10\text{V}$.

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case (junction-heat spreader)	R_{thJC}	3.6	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	52	

Electrical Characteristic (at $T_j = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	60	-	-	V	$V_{GS}=0V, I_D=250\mu A$
		60	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{GS(th)}$	1.0	-	2.5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=60V, V_{GS}=0V$ $T_j=25^\circ\text{C}$
		-	-	100		$T_j=125^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	9.6	13.0	mΩ	$V_{GS}=10V, I_D=20A, T_j=25^\circ\text{C}$
		-	12.7	19.1		$V_{GS}=4.5V, I_D=16A, T_j=25^\circ\text{C}$
Transconductance	g_{fs}	-	51	-	S	$V_{DS}=5V, I_D=20A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	944	-	pF	$V_{GS}=0V, V_{DS}=30V, f=1MHz$
Output Capacitance	C_{oss}	-	280	-		
Reverse Transfer Capacitance	C_{rss}	-	11	-		
Gate Total Charge	Q_G	-	17	-	nC	$V_{GS}=10V, V_{DS}=30V, I_D=20A, f=1MHz$
Gate-Source charge	Q_{gs}	-	4	-		
Gate-Drain charge	Q_{gd}	-	3	-		
Turn-on delay time	$t_{d(on)}$	-	6	-	ns	$V_{GS}=10V, V_{DD}=30V,$ $R_{G_ext}=3\Omega, I_D=20A$
Rise time	t_r	-	63	-		
Turn-off delay time	$t_{d(off)}$	-	18	-		
Fall time	t_f	-	7	-		
Gate resistance	R_G	-	1.7	-	Ω	$V_{GS}=0V, V_{DS}=0V, f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Diode continuous forward current	I_S	-	-	30	V	$T_c = 25^{\circ}\text{C}$
Diode pulse current	I_S pulse	-	-	120	V	$T_c = 25^{\circ}\text{C}$
Body Diode Forward Voltage	V_{SD}	-	0.9	1.4	V	$V_{GS}=0V, I_{SD}=20A$
Body Diode Reverse Recovery Time	t_{rr}	-	50	-	ns	$I_F=20A, dI/dt=300A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	20	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

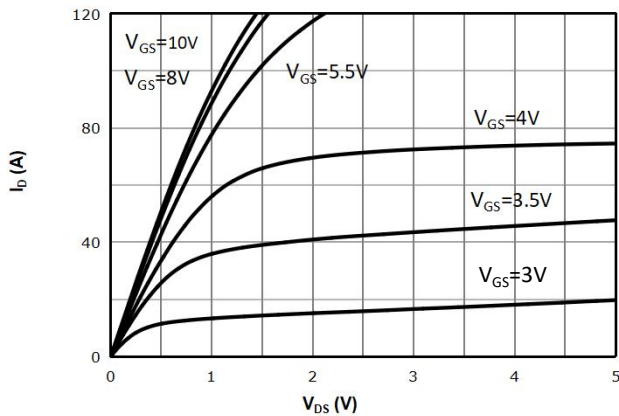


Fig 2: Transfer Characteristics

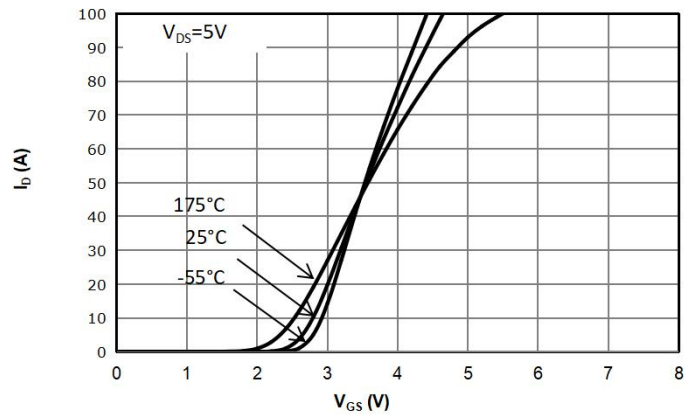
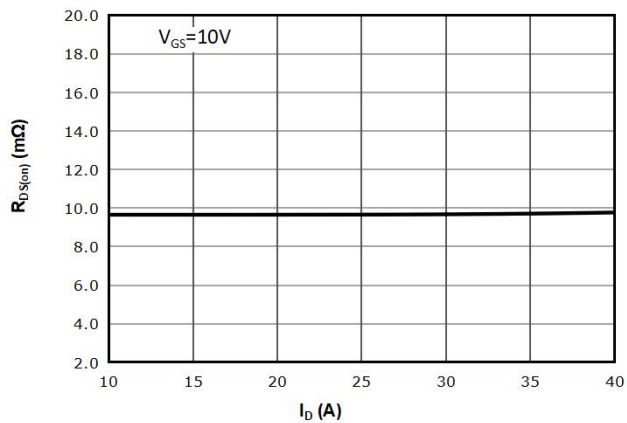
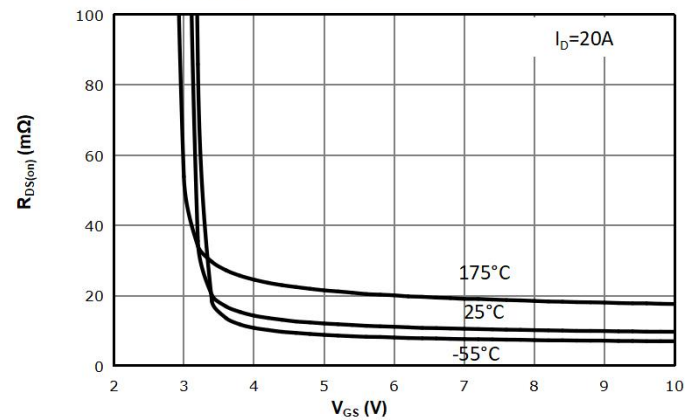
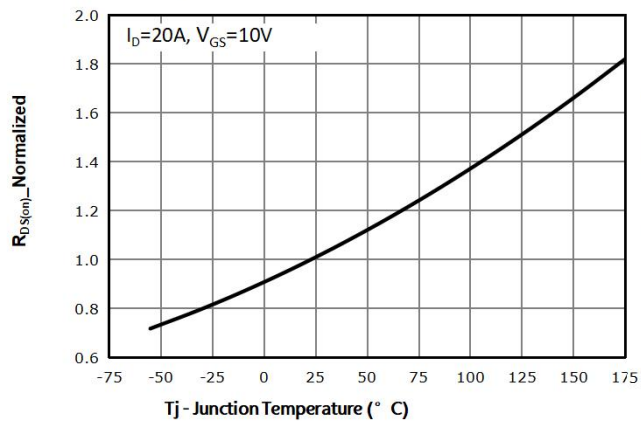
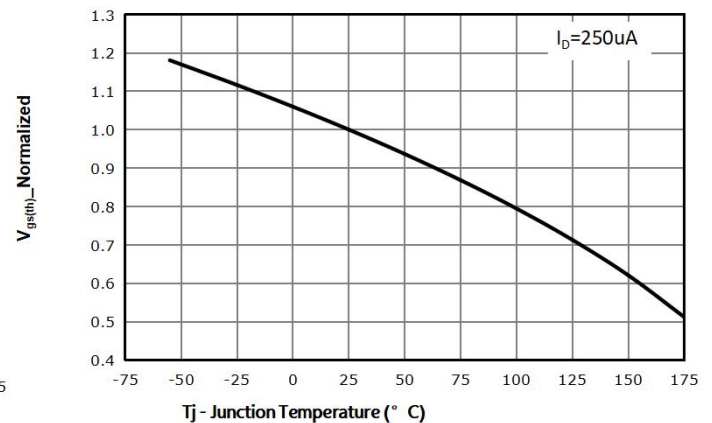

 Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

 Fig 4: $R_{DS(on)}$ vs Gate Voltage

 Fig 5: $R_{DS(on)}$ vs. Temperature

 Fig 6: $V_{GS(th)}$ vs. Temperature


Fig 7: BVdss vs. Temperature

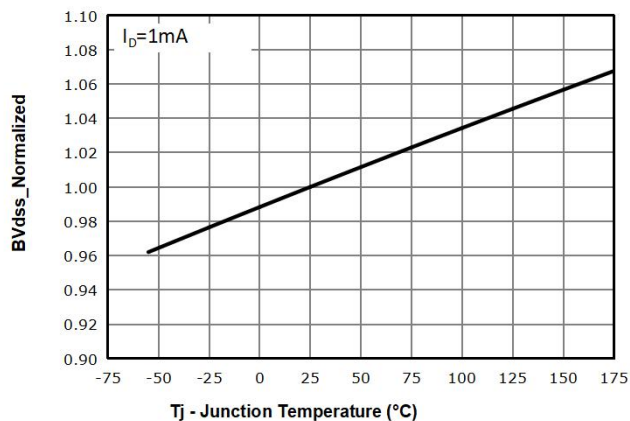


Fig 8: Capacitance Characteristics

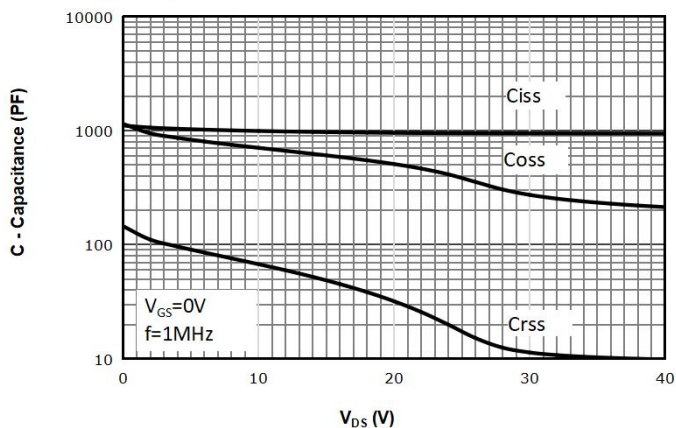


Fig 9: Gate Charge Characteristics

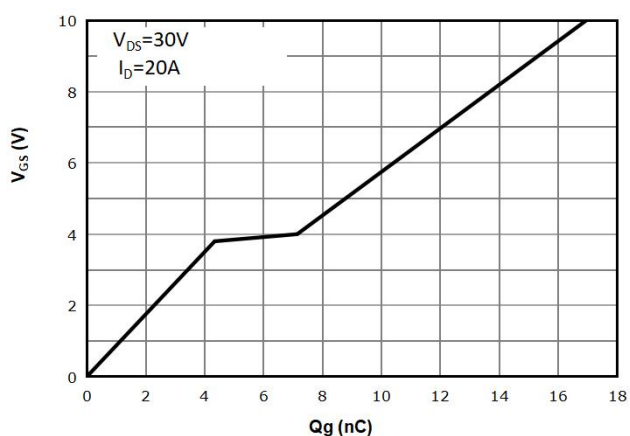


Fig 10: Body-diode Forward Characteristics

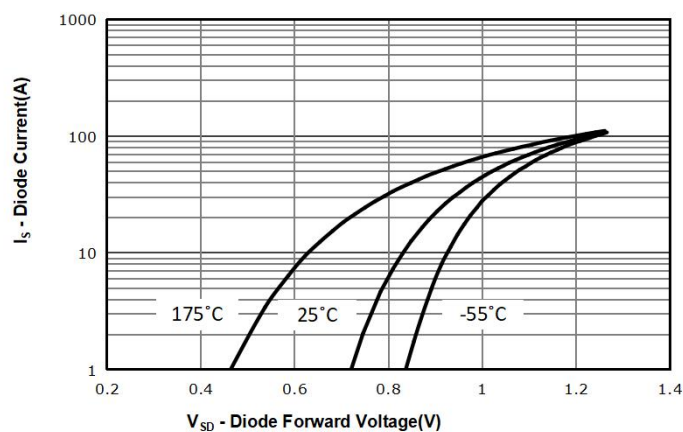


Fig 11: Power Dissipation

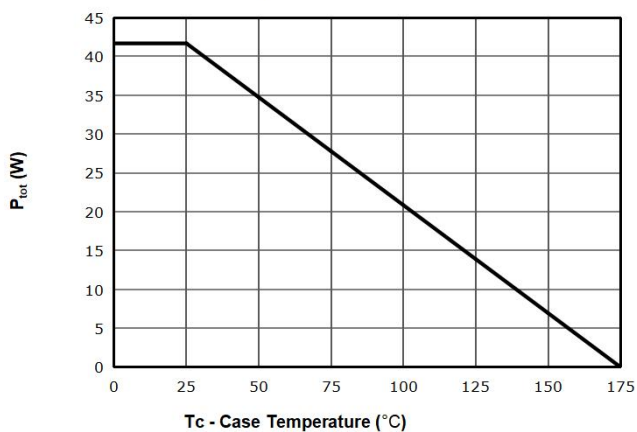


Fig 12: Drain Current Derating

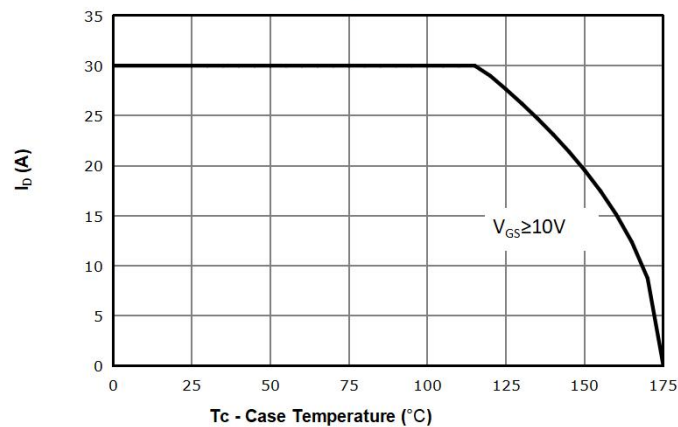


Fig 13: Safe Operating Area

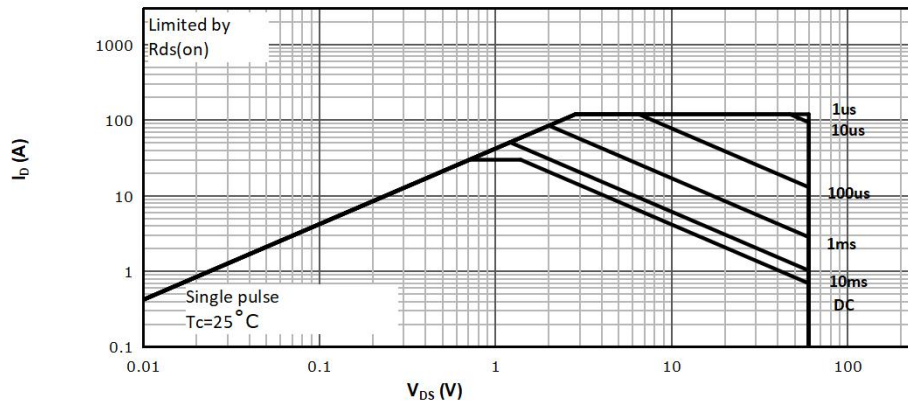
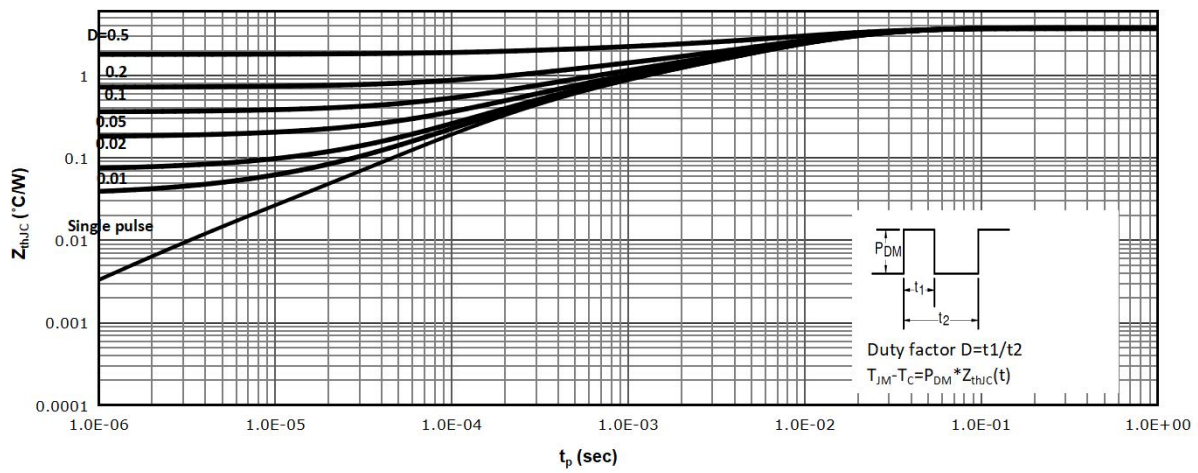
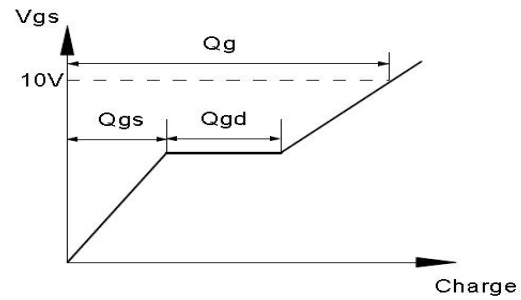
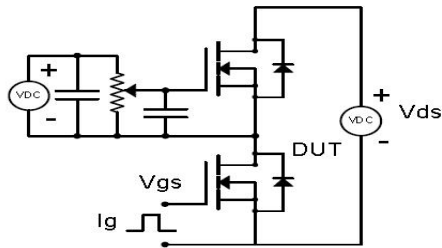


Fig 14: Max. Transient Thermal Impedance

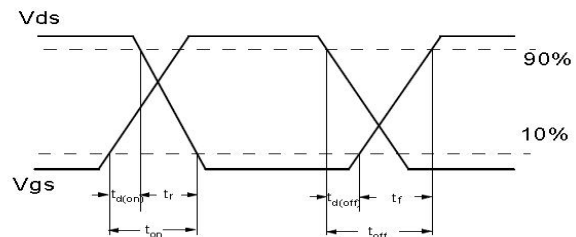
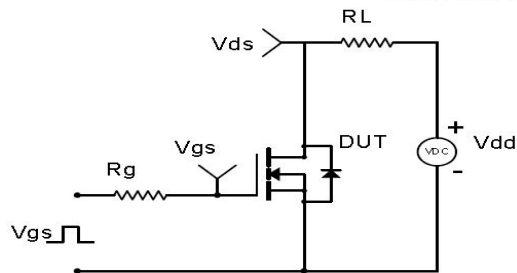


Test Circuit & Waveform

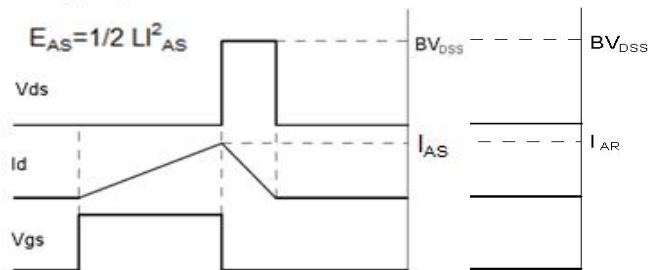
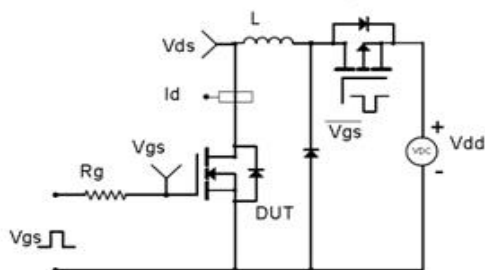
Gate Charge Test Circuit & Waveform



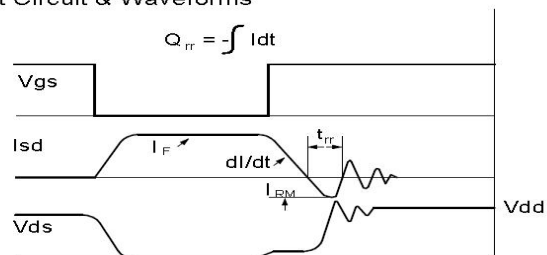
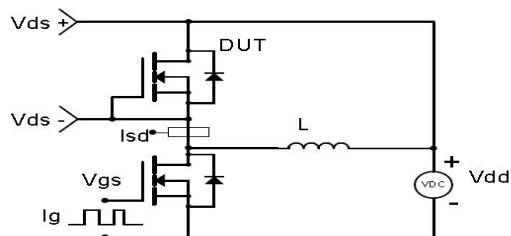
Resistive Switching Test Circuit & Waveforms

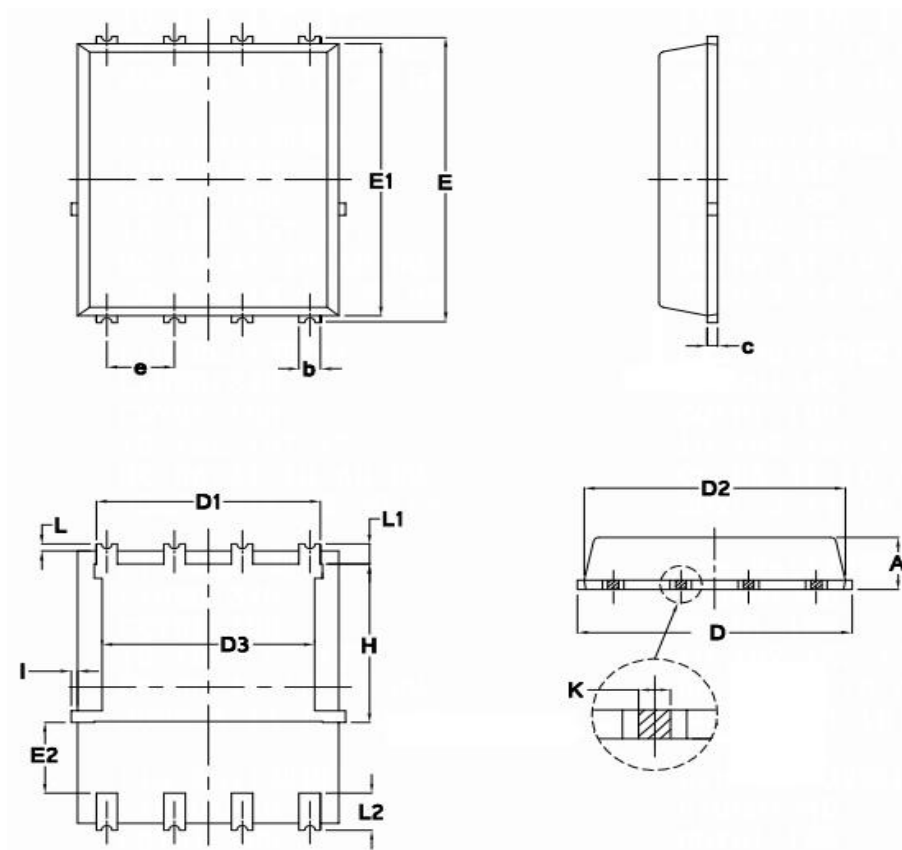


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: PDFN5x6-WF Type P


Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min.	NOM.	Max.	Min.	NOM.	Max.
A	0.90	1.10	1.20	0.035	0.043	0.047
b	0.31	0.41	0.51	0.012	0.016	0.020
c	0.15	0.20	0.30	0.006	0.008	0.012
D	4.80	4.98	5.15	0.189	0.196	0.203
D1	3.91	4.22	4.36	0.154	0.166	0.172
D2	4.80	4.90	5.00	0.189	0.193	0.197
D3	3.85	4.00	4.15	0.152	0.157	0.163
E	5.90	6.05	6.15	0.232	0.238	0.242
E1	5.65	5.76	5.85	0.222	0.227	0.230
E2	1.10	-	-	0.043	-	-
e	1.27 BSC			0.050 BSC		
L	0.05	0.15	0.25	0.002	0.006	0.010
L1	0.38	0.43	0.50	0.015	0.017	0.020
L2	0.51	0.79	0.86	0.020	0.031	0.034
H	3.25	3.35	3.58	0.128	0.132	0.141
I	0.00	-	0.18	0.000	-	0.007
K	Φ0.20 REF			Φ0.0079 REF		

Marking**NOTE:**

XAAAAAAAA -Y

X

—Assembly location code

AAAAAAA

—Assembly lot NO. last 7digits

Y

—Bin code

Revision History

Revision	Date	Major changes
1.0	2025/3/10	Release of preliminary version.

Disclaimer

CRM reserves the right to change any product or information in this Specification at any time without prior notice.

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